

FDP090N10 N-Channel PowerTrench[®] MOSFET 100 V, 75 A, 9 mΩ

Features

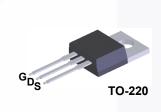
- $R_{DS(on)}$ = 7.2 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 75 A
- · Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$
- High Power and Current Handling Capability
- RoHS Compliant

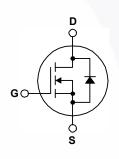
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Micor Solar Inverter





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FDP090N10	Unit
V _{DSS}	Drain to Source Voltage			100	V
V _{GSS}	Gate to Source Voltage			±20	V
ID	Drain Current	- Continuous (T _C = 85 ^o C)		75	Α
I _{DM}	Drain Current	- Pulsed (Note 1)		300	Α
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		(Note 2)	309	mJ
I _{AR}	Avalanche Current (Note 1)		(Note 1)	75	Α
E _{AR}	Repetitive Avalanche Energy		(Note 1)	20.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3		(Note 3)	5.6	V/ns
P _D	Devues Dissinction	$(T_{\rm C} = 25^{\rm o}{\rm C})$		208	W
	Power Dissipation	- Derate Above 25°C		1.39	W/ºC
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +175	°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		nds	300	°C

Thermal Characteristics

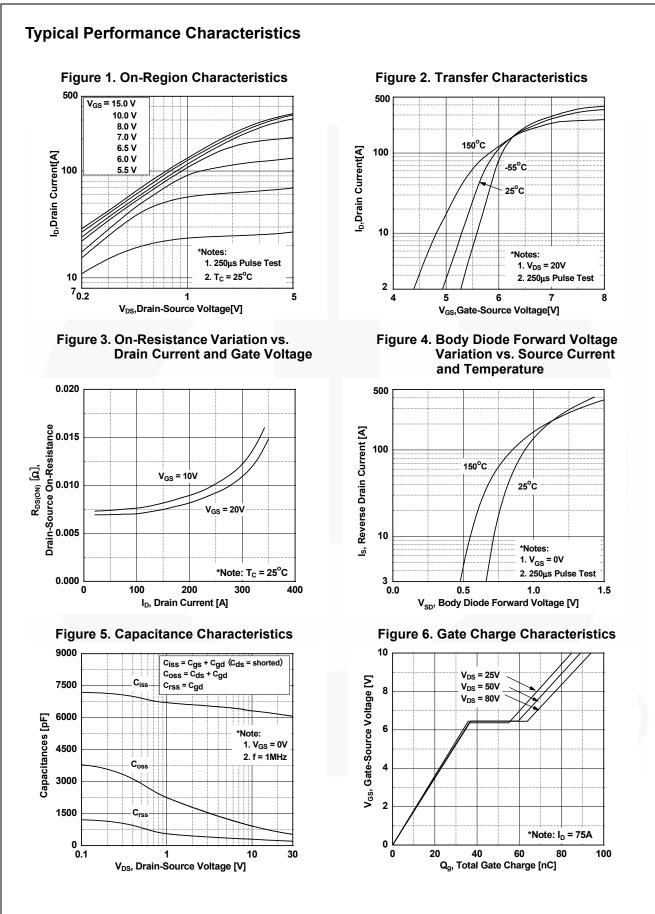
Symbol	Parameter	FDP090N10	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.72	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	°C/vv

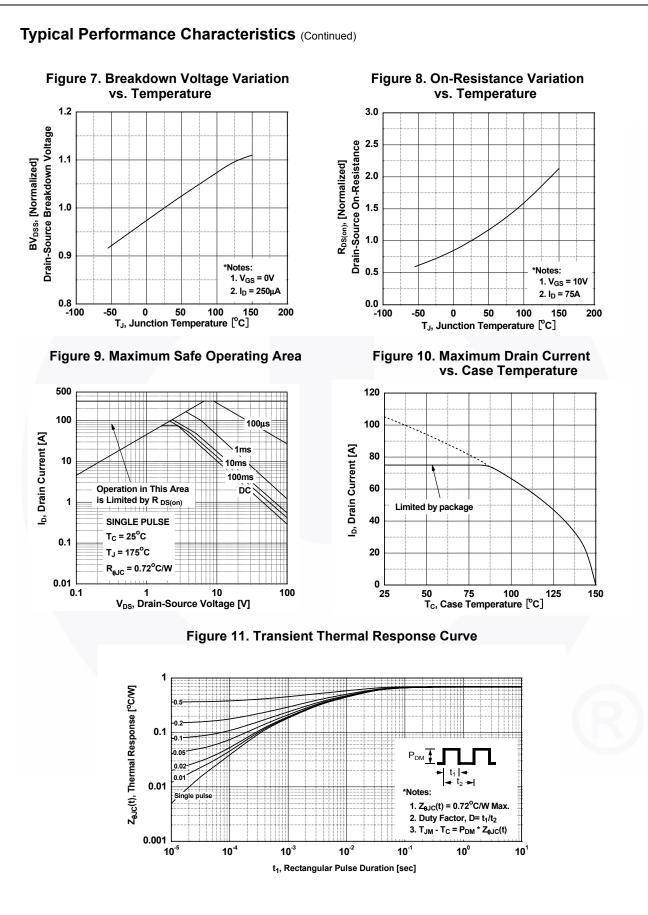
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November 2013

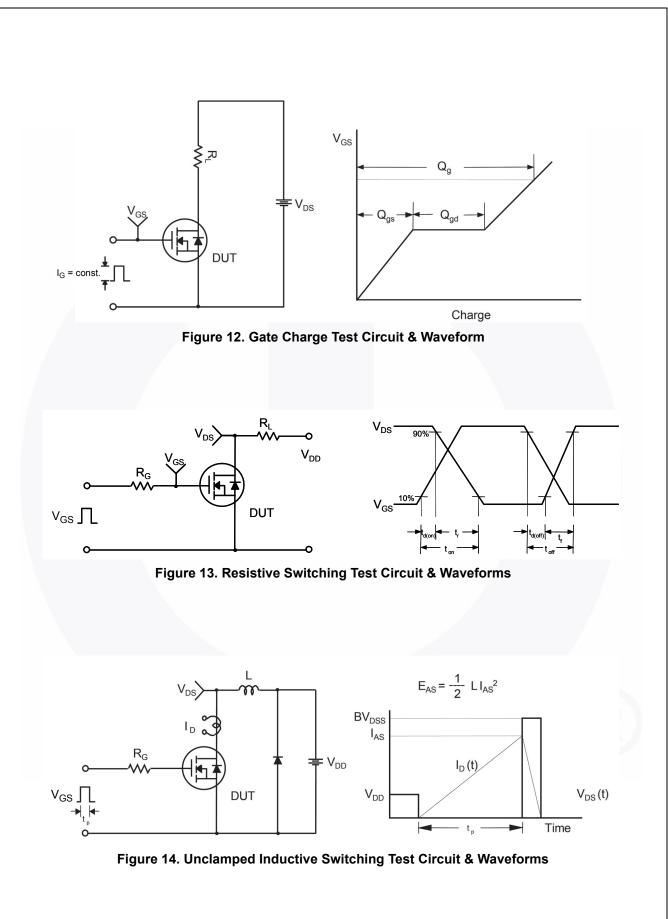
FDP090N10 -
- N-Channel P
owerTrench [®]
MOSFET

		Package	Packing Method	Reel Size	Таре	Width	Quar	ntity	
		TO-220	Tube	N/A	N/A		50 units		
Electrica	Char	acteristics T _c =	25°C unless	otherwise noted.					
Symbol		Parameter		Test Condit	tions	Min.	Тур.	Max.	Unit
Off Charac	torietic	e						I	
			Itogo	1 - 250 + 0.1(0.1)	-25°	100			V
BV _{DSS} ΔBV _{DSS}		o Source Breakdown Vo own Voltage Temperatu		$I_{\rm D}$ = 250 µA, $V_{\rm GS}$ = 0		100	-	-	V
ΔDV _{DSS} /ΔTJ	Coeffici			I_D = 250 μ A, Reference	ced to 25°C	-	0.1	-	V/ºC
				V _{DS} = 100 V, V _{GS} = 0 V		-	-	1	
DSS	Zero G	ate Voltage Drain Curre	nt	V _{DS} = 100 V, V _{GS} = 0		-	-	500	μA
I _{GSS}	Gate to	Body Leakage Current		V_{GS} = ±20 V, V_{DS} = 0	V	-	-	±100	nA
On Charac	teristic	S							
V _{GS(th)}	Gate TI	nreshold Voltage		V _{GS} = V _{DS} , I _D = 250 µ	ιA	2.5	3.5	4.5	V
R _{DS(on)}	Static D	rain to Source On Resi	stance	V _{GS} = 10 V, I _D = 75 A		-	7.2	9	mΩ
9 _{FS}	Forwar	d Transconductance		V _{DS} = 10 V, I _D = 37.5	A	-	100	-	S
Dynamic C	haracte	eristics							
C _{iss}	Input C	apacitance		V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		-	6185	8225	pF
C _{oss}	Output	Capacitance				-	585	775	pF
C _{rss}	Reverse	e Transfer Capacitance				-	235	355	pF
Switching	Charac	teristics							
t _{d(on)}	1	n Delay Time					107	224	ns
t _r	Turn-Or	n Rise Time		V _{DD} = 50 V, I _D = 75 A		-	322	655	ns
t _{d(off)}	Turn-Of	f Delay Time		$V_{GS} = 10 \text{ V}, \text{ R}_{G} = 25 \Omega$		-	166	342	ns
t _f	Turn-Of	f Fall Time			(Note 4)	-	149	309	ns
Q _{g(tot)}	Total Ga	ate Charge at 10V		V _{DS} = 50 V, I _D = 75 A			89	116	nC
Q _{gs}	Gate to	Source Gate Charge		$V_{GS} = 10 V$,	-	37	-	nC
Q _{gd}	Gate to	Drain "Miller" Charge			(Note 4)	-	22	-	nC
	ce Dio	de Characteristics	6					1	
I _S	Maximum Continuous Drain to Source Diode Forward Current				-	-	75	Α	
I _{SM}	Maximu	m Pulsed Drain to Sour	ce Diode For	ward Current		-	-	300	Α
V _{SD}	Drain to Source Diode Forward Voltage			V _{GS} = 0 V, I _{SD} = 75 A		-	-	1.25	V
t _{rr}	Reverse Recovery Time			$V_{GS} = 0 V, I_{SD} = 75 A,$		-	73	-	ns
Q _{rr}	Reverse Recovery Charge			dI _F /dt = 100 A/µs		-	166	-	nC
Notes: 1: Repetitive rating 2: L = 0.11 mH, I_{AS} 3: $I_{SD} \leq 75$ A, di/d	: pulse-widt _S = 75 A, V _D : ≤ 200 A/μs	h limited by maximum junction 1 $_{D} = 50 V, R_{G} = 25 \Omega$, starting T , $V_{DD} \le BV_{DSS}$, starting T _J = 25 perating temperature typical ch	_J = 25°C. °C.					E	3





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DUT + V_{DS} a ۱_{sD} م L Driver R_G, Same Type as DUT L F ∨_{DD} $\prod V_{GS}$ • dv/dt controlled by R_{G} • I_{SD} controlled by pulse period Î Gate Pulse Width $\mathbf{V}_{\mathbf{GS}}$ D = Gate Pulse Period 10V (Driver) I_{FM}, Body Diode Forward Current I _{SD} di/dt (DUT) I_{RM} Body Diode Reverse Current V_{DS} (DUT) Body Diode Recovery dv/dt V_{SD} V_{DD} Body Diode Forward Voltage Drop Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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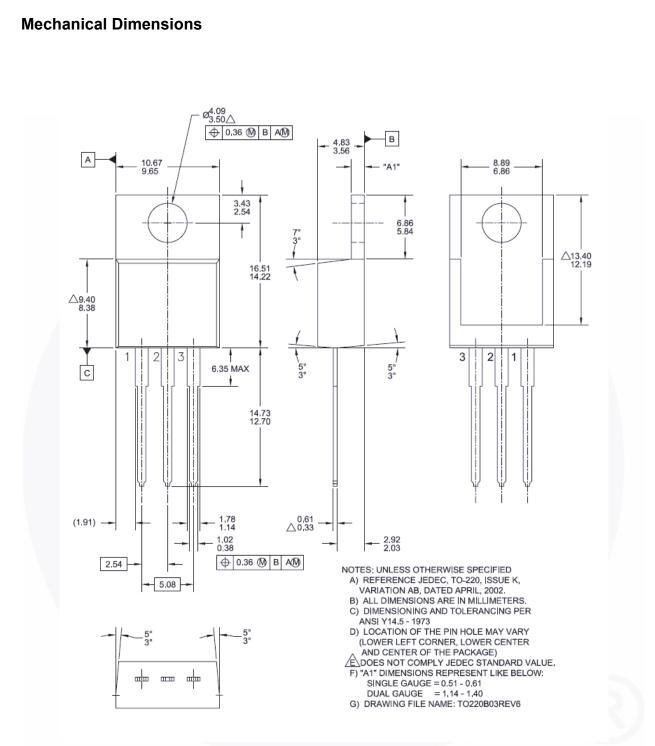


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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